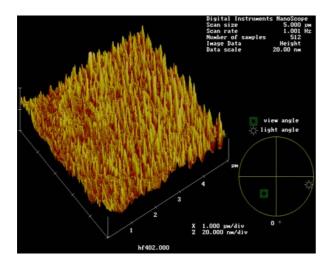


view angle light angle

X 1.000 pm/div Z 20.000 pm/div



Fig. 2-48 AFM micrographs of excimer laser crystallized poly-Silicon films surface roughness. The applied laser energy densities are (a) 310, (b) 360mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for 30sec



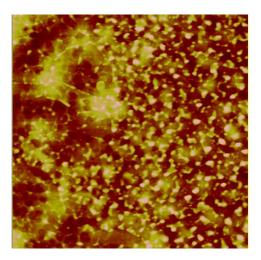
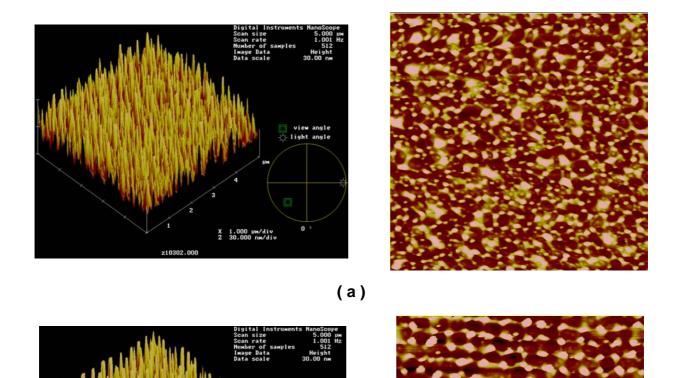




Fig. 2-48AFM micrographs of excimer laser crystallized poly-Silicon films surface
roughness. The applied laser energy densities are (c) 400 mJ/cm². The
laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec,
pitch 0.02mm, beam width 0.4mm, pre treatment clean with HF 1% for
30sec

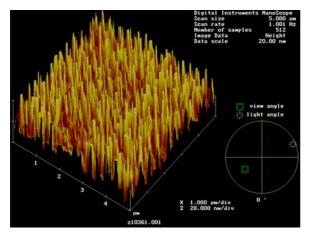






view angle light angle

Fig. 2-49 AFM micrographs of excimer laser crystallized poly-Silicon films surface roughness. The applied laser energy densities are (a) 300, (b) 340, mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with O3 20ppm for 100sec



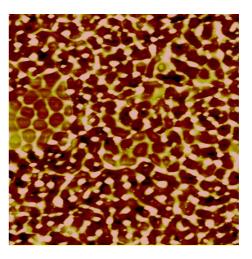
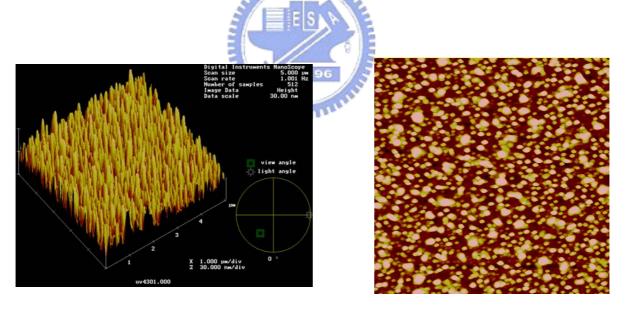




Fig. 2-49 AFM micrographs of excimer laser crystallized poly-Silicon films surface roughness. The applied laser energy densities are (c) 360 mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with O3 20ppm for 100sec



(a)

Fig. 2-50 AFM micrographs of excimer laser crystallized poly-Silicon films surface roughness. The applied laser energy densities are (a) 300mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with UV exposure λ254nm for 400sec

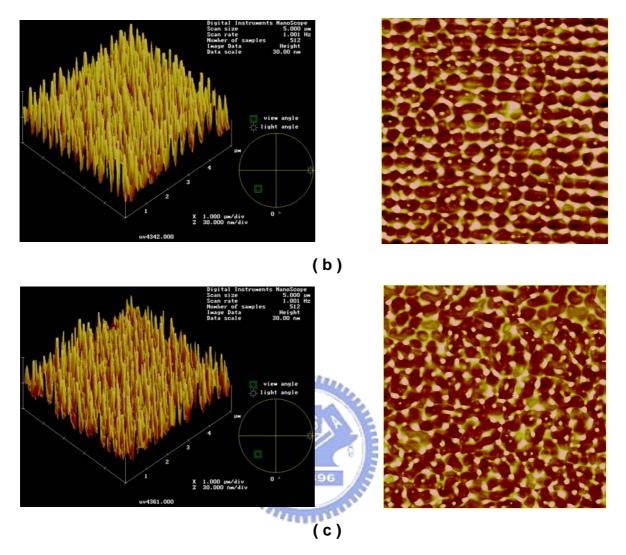


Fig. 2-50 AFM micrographs of excimer laser crystallized poly-Silicon films surface roughness. The applied laser energy densities are (b) 340, (c) 360 mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with UV exposure λ254nm for 400sec